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Amendments to the claims:

1-29. (canceled)

30. (currently amended) A method of simultaneously burning in a plurality of active semiconductor surface emitting laser devices on a wafer for burning in a wafer having a plurality of active semiconductor surface emitting laser devices, each of said laser devices having a first electrode on said first side of said wafer and a second electrode on a second side of said wafer, said wafer further having an insulating layer formed on a first side of said wafer over said first electrodes, said method comprising the steps of:

providing a wafer having a plurality of active semiconductor surface emitting laser devices formed thereon, each of said laser devices having a first electrode on a first side of the wafer and a second electrode on a second side of the wafer;

depositing a temporary insulating layer on a first side of said wafer;

selectively forming vias through said insulating layer to expose said first electrode of at least two of said plurality of laser devices;

depositing a temporary electrically conductive interconnect layer over said insulating layer whereby said first electrodes of said at least two of said plurality of active laser devices are coupled together to provided with a common electrical contact;

applying a predetermined power to said interconnect layer whereby said predetermined power is simultaneously applied to said first electrodes of said at least two of said plurality of active laser devices;

identifying defective ones of said plurality of active laser devices; and

completely removing said ~~temporary~~ insulating layer and said temporary interconnect layer.

31. (previously added) The method of claim 30 wherein said step of depositing said interconnect layer further comprises the step of processing said interconnect layer to form one or more common contact traces, wherein said one or more contact traces electrically couple together said first electrodes of said at least two of said plurality of active

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32. (previously added) The method of claim 31 wherein said step of processing further comprises forming a resistor between said one or more contact traces and said first electrodes.

33. (previously added) The method of claim 32 wherein said step of forming said resistor comprises forming a resistive bridge.

34. (previously added) The method of claim 31 wherein said step of processing further comprises forming a fuse between said one or more contact traces and said first electrodes.